

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1-4.

5. (New) A method for producing a silicon wafer having a crystal orientation $\langle 110 \rangle$ from a silicon single crystal ingot grown by Floating Zone method (FZ method), wherein, at least, an FZ silicon single crystal ingot is grown by being made to be dislocation-free by Dash Necking method using a seed crystal having its crystal axis inclined at a specified angle from a crystal orientation $\langle 110 \rangle$, and the grown FZ silicon single crystal ingot is sliced at the just angle of a crystal orientation $\langle 110 \rangle$ to produce a silicon wafer having a crystal orientation $\langle 110 \rangle$.

6. (New) The method for producing a silicon wafer according to Claim 5, wherein the sliced silicon wafer having a crystal orientation $\langle 110 \rangle$ is made to be a perfect circle by processing of chamfering.

7. (New) The method for producing a silicon wafer according to Claim 5, wherein the specified angle of inclining the seed crystal is 1° to 30° .

8. (New) The method for producing a silicon wafer according to Claim 6, wherein the specified angle of inclining the seed crystal is 1° to 30° .

9. (New) The silicon wafer having a crystal orientation $\langle 110 \rangle$ produced by the method of producing a silicon wafer according to Claim 5.
10. (New) The silicon wafer having a crystal orientation $\langle 110 \rangle$ produced by the method of producing a silicon wafer according to Claim 6.
11. (New) The silicon wafer having a crystal orientation $\langle 110 \rangle$ produced by the method of producing a silicon wafer according to Claim 7.
12. (New) The silicon wafer having a crystal orientation $\langle 110 \rangle$ produced by the method of producing a silicon wafer according to Claim 8.